



### N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
60V	$8.0 \text{m}\Omega$ @ $V_{GS} = 10V$	130A

### Features and Benefits

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching-Ensures More Reliable and Robust End Application
- Low Input Capacitance
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

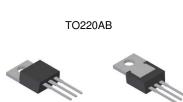
## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Motor Control
- Backlighting
- DC-DC Converters
- **Power Management Functions**

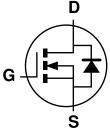
### Mechanical Data

- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)

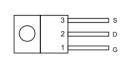


Top View

**Bottom View** 



Equivalent Circuit



Top View Pin Out Configuration

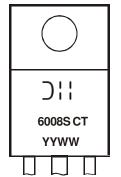
## **Ordering Information (Note 5)**

Part Number	Case	Packaging
DMNH6008SCTQ	TO220AB	50 Pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



6008SCT = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week (01 to 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	60	V
Gate-Source Voltage			$V_{GSS}$	20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ID	130 90	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	200	Α
Maximum Continuous Body Diode Forward Current (Note 6)			Is	80	Α
Avalanche Current (Note 7) L=0.1mH			I <sub>AS</sub>	62	Α
Avalanche Energy (Note 7) L=0.1mH			Eas	190	mJ

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$	PD	210 100	W
Thermal Resistance, Junction to Case (Note 6)	R <sub>OJC</sub>	0.7	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	$BV_{DSS}$	60		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_		1	μΑ	$V_{DS} = 48V$ , $V_{GS} = 0V$	
Gate-Source Leakage	IGSS		_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	2		4	<b>V</b>	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	6.0	8.0	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.2	V	$V_{GS} = 0V$ , $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>ISS</sub>	_	2,596	_		V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V f = 1.0MHz	
Output Capacitance	Coss	_	437	_	рF		
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	118	_			
Gate Resistance	Rg	_	2.0	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>		40	_			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_{G}$	_	21	_	nC	V <sub>DD</sub> = 30V, I <sub>D</sub> = 20A	
Gate-Source Charge	Q <sub>GS</sub>		8.3	_	IIC		
Gate-Drain Charge	$Q_{GD}$	_	11.8	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	5.7	_		$V_{DD} = 30V, V_{GS} = 10V,$ $R_G = 1\Omega, I_D = 20A$	
Turn-On Rise Time	t <sub>R</sub>	_	5.0	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	15.6	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	3.4	_			
Reverse Recovery Time	t <sub>RR</sub>	_	33	_	ns	1 20A di/dt 100A/vo	
Reverse Recovery Charge	Q <sub>RR</sub>	_	33	_	nC	$I_F = 20A$ , di/dt = 100A/ $\mu$ s	

Notes: 6. Device mounted on an infinite heatsink.

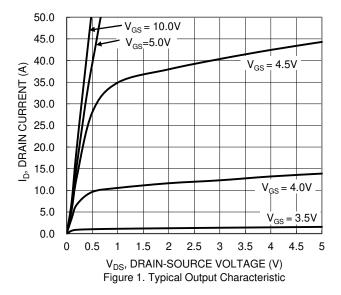
<sup>7.</sup>  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_{J} = +25^{\circ}C$ .

<sup>8.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>9.</sup> Guaranteed by design. Not subject to product testing.







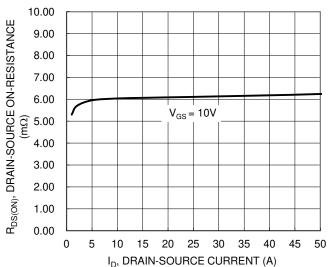


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

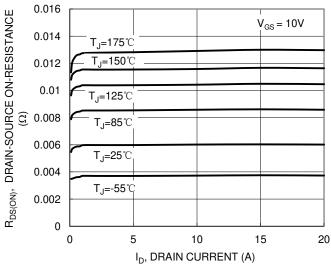
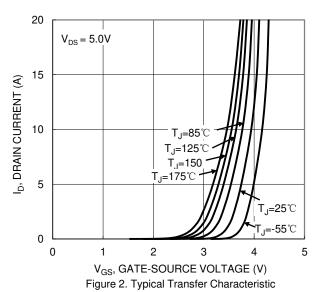


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



 $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE ( $m\Omega$ )  $I_D = 20A$ V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

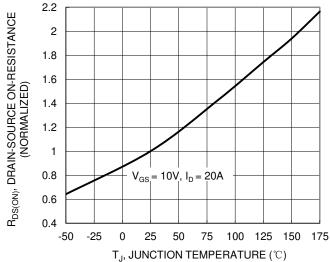


Figure 6. On-Resistance Variation with Temperature





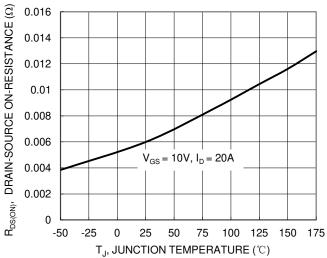


Figure 7. On-Resistance Variation with Temperature

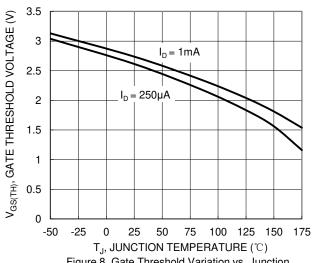


Figure 8. Gate Threshold Variation vs. Junction Temperature

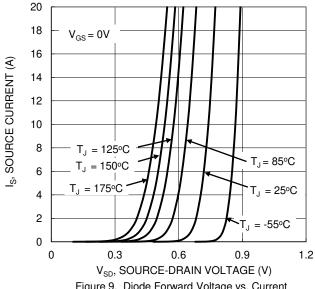
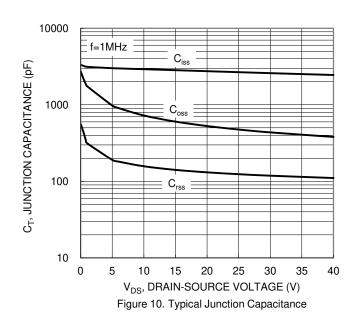
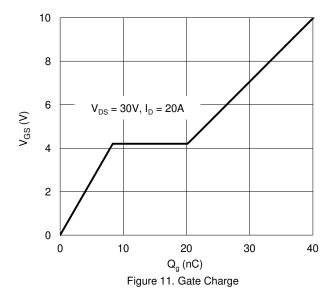


Figure 9. Diode Forward Voltage vs. Current

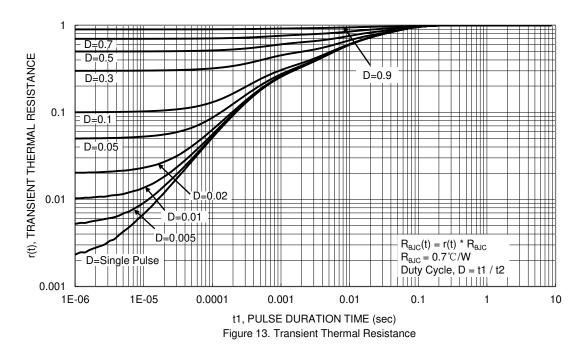


1000 R<sub>DS(ON)</sub> Limited 100 I<sub>D</sub>, DRAIN CURRENT (A) =10µs 10  $P_W = 10 ms$ P =100ms 1  $T_{J(Max)} = 175^{\circ}C$   $T_C = 25^{\circ}C$  Single Pulse DUT on Infinite Heatsink  $V_{GS} = 1.0 V$ 0.01 0.1 10 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



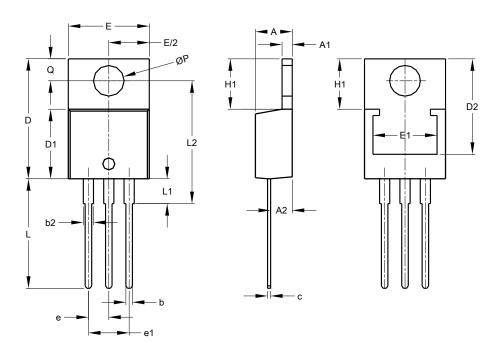




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### TO220AB



TO220AB						
Dim	Min	Max	Тур			
Α	3.56	4.82	_			
<b>A</b> 1	0.51	1.39	_			
A2	2.04	2.92	_			
b	0.39	1.01	0.81			
b2	1.15	1.77	1.24			
С	0.356	0.61				
D	14.22	16.51	_			
D1	8.39	9.01	_			
D2	11.45	12.87	_			
е		_	2.54			
e1	_	_	5.08			
Е	9.66	10.66	_			
E1	6.86	8.89	_			
H1	5.85	6.85	_			
L	12.70	14.73				
L1	_	4.42	_			
L2	15.80	17.51	16.00			
Р	3.54	4.08	_			
Q	2.54	3.42	_			
All Dimensions in mm						



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